

**Amendments to the Abstract**

Please replace the paragraph at page 9, lines 3 through 25 with the following amended paragraph:

A circuit which accurately controls the word line (pass transistor gate) driving voltage to a voltage which is both controlled and is not significantly greater than is needed to drive the word line. ~~The elements of the present invention~~ circuit ~~eliminates~~ the need for a double-bootstrapping circuit, and ensures that no voltages exceed that necessary to fully turn on a memory cell access transistor. ~~Accordingly, voltage~~ Voltages in excess of that which would reduce reliability are avoided, and accurate driving voltages are obtained. A DRAM ~~is comprised of~~ includes word lines, memory cells having enable inputs connected to the word lines, ~~apparatus~~ for a gate receiving word line selecting signals at first logic levels  $V_{ss}$  and  $V_{dd}$ , and for providing a select signal at levels  $V_{ss}$  and  $V_{dd}$ , a high voltage supply source  $V_{pp}$  which is higher in voltage than  $V_{dd}$ , a circuit for translating the select signals at levels  $V_{ss}$  and  $V_{dd}$  to levels  $V_{ss}$  and  $V_{pp}$  and for applying it directly to the word lines ~~for application to the enable inputs~~ whereby an above  $V_{dd}$  voltage level word line is achieved without the use of double boot-strap circuits.